

filed 11/12/1999

(2-92)

Sheet 1 of 1

Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION <i>(Use several sheets if necessary)</i>	Docket Number (Optional) 2919.1US (96-0499.01)	Application Number <u>07/</u> To be assigned <u>072935</u>
	Applicant <u>Pai-Hung Pan</u>	
	Filing Date <u>May 5, 1998</u>	Group Art Unit <u>To be assigned</u> <u>2823</u>

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	NAME	DATE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<u>G</u>	4,786,954	Morie et al.	11/22/88	—	—	
<u>G</u>	4,849,344	Desbiens et al.	07/18/89	—	—	
<u>G</u>	5,173,439	Dash et al.	12/22/92	—	—	
<u>G</u>	5,272,117	Roth et al.	12/21/93	—	—	
<u>G</u>	5,296,392	Gula et al.	03/22/94	—	—	
<u>G</u>	5,297,082	Lee	03/22/94	—	—	
<u>G</u>	5,346,587	Doan et al.	09/13/94	—	—	
<u>G</u>	5,433,794	Fazan et al.	07/18/95	—	—	
<u>G</u>	5,436,488	Poon et al.	07/25/95	—	—	
<u>G</u>	5,459,096	Venkatesan et al.	10/17/95	—	—	
<u>G</u>	5,492,858	Bose et al.	02/20/96	—	—	
<u>G</u>	5,516,625	McNamara et al.	05/14/96	—	—	
<u>G</u>	5,516,721	Galli et al.	05/14/96	—	—	
<u>G</u>	5,521,422	Mandelman et al.	05/28/96	—	—	

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

<u>G</u>		Davari, et al., "A Variable-Size Shallow Trench Isolation (STI) Technology With Diffused Sidewall Doping For Submicron CMOS", <i>IEEE IEDM</i> (1988).
<u>G</u>		K. Blumenstock et al., "Shallow Trench Isolation for Ultra-Large-Scale Integrated Devices", <i>J. Vac. Sci. Technol.</i> , B 12(1) (Jan/Feb 1994).

EXAMINER <u>FOURSON</u>	DATE CONSIDERED <u>11/7/99</u> <u>7/25/06</u>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

IDS filed 5/5/1998

as defined in 37 C.F.R. § 1.56(b). Further, no representation is made by Applicant herein that no other possible material information as defined in 37 C.F.R. § 1.56 (b) exists.

DOCUMENTS

U.S. Patent Documents

	<u>U.S. Patent No.</u>	<u>Inventor</u>	<u>Issue Date</u>
G	4,786,954	Morie et al.	11/22/88
	4,849,344	Desbiens et al.	07/18/89
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Other Documents

G Davari, et al., "A Variable-Size Shallow Trench Isolation (STI) Technology With Diffused Sidewall Doping For Submicron CMOS", *IEEE IEDM* (1988).

G K. Blumenstock et al., "Shallow Trench Isolation for Ultra-Large-Scale Integrated Devices", *J. Vac. Sci. Technol.*, B 12(1) (Jan/Feb 1994).

EX. FOURSON

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